

**ABSTRACT OF THE DISCLOSURE**

The invention provides a transistor capable of achieving a higher speed although its construction is easy to manufacture without requiring wiring to intersect three-dimensionally even if unit elements of transistors are connected in parallel, and to provide an electronic device. The transistor can include common collector wiring provided on an insulating substrate, a first layer, which is provided on the common collector wiring which is made of an N-type semiconductor, a second layer, made of a P-type semiconductor, provided on the first layer, a third layer, which is provided on the second layer and which is made of an N-type semiconductor, common base wiring, which is provided on the insulating substrate and which is connected to the second layer, and common emitter wiring, which is provided on the insulating substrate and which is connected to the third layer.